



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92L Plastic-Encapsulate Transistors

KSC2331 TRANSISTOR (NPN)

FEATURE

Power dissipation

$P_{CM} : 1 \quad W \quad (T_{amb}=25^{\circ}C)$

Collector current

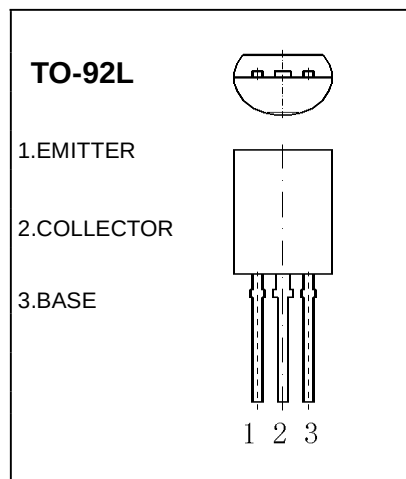
$I_{CM} : 0.7 \quad A$

Collector-base voltage

$V_{(BR)CBO} : 80 \quad V$

Operating and storage junction temperature range

$T_J, T_{stg} : -55^{\circ}C \text{ to } +150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 mA, I_B = 0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10 \mu A, I_C = 0$	8			V
Collector cut-off current	I_{CBO}	$V_{CB} = 60 V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 V, I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 2 V, I_C = 50 mA$	40		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 mA, I_B = 50 mA$			0.7	V
Base-emitter voltage	$V_{BE(sat)}$	$I_C = 500 mA, I_B = 50 mA$			1.2	V
Collector output capacitance	C_{ob}	$(V_{CB} = 10 V, I_E = 0, f = 1 MHz)$		8		pF
Transition frequency	f_T	$V_{CE} = 10 V, I_C = 50 mA$	30			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y
Range	40-80	70-140	120-240